

# 2SJ0674G

## Silicon P-channel MOS FET

For switching circuits

### ■ Features

- Low ON resistance  $R_{on}$
- High-speed switching
- SSSMini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

### ■ Package

- Code  
SSSMini3-F2
- Pin Name  
1: Gate  
2: Source  
3: Drain

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	$V_{DSS}$	-30	V
Gate-source surrender voltage	$V_{GSS}$	$\pm 12$	V
Drain current	$I_D$	-100	mA
Peak drain current	$I_{DP}$	-200	mA
Power dissipation	$P_D$	100	mW
Channel temperature	$T_{ch}$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

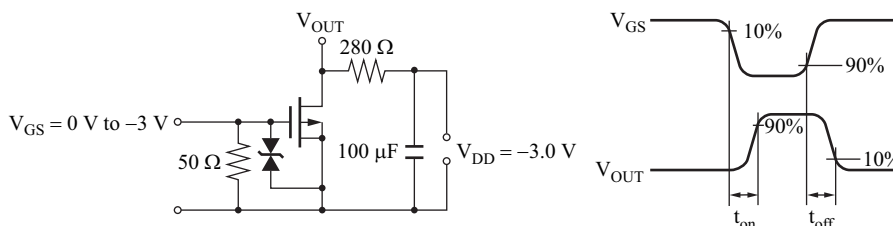
### ■ Marking Symbol: 5U

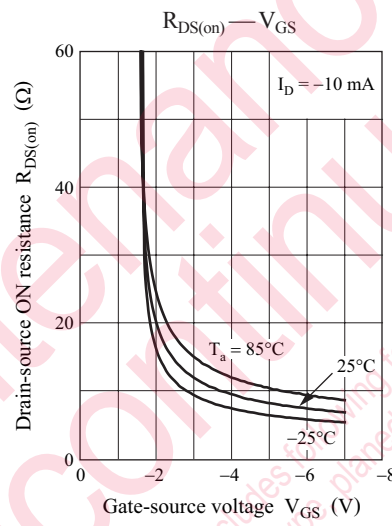
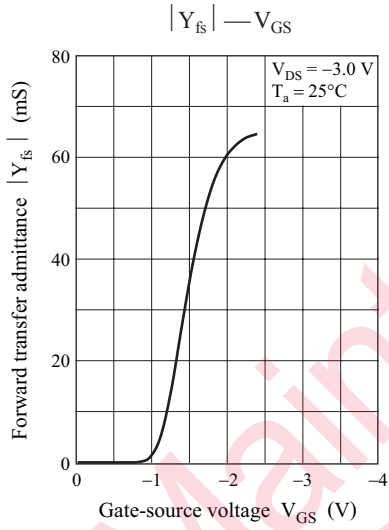
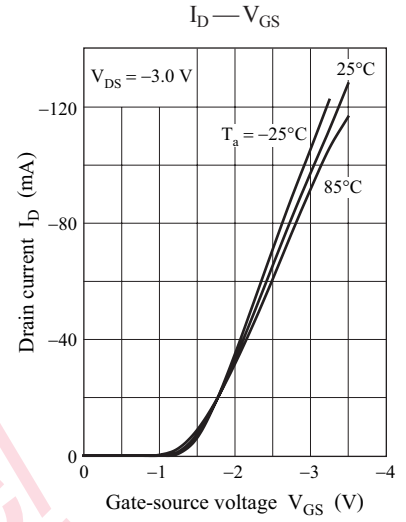
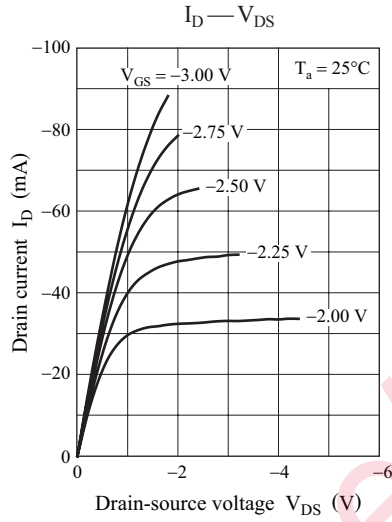
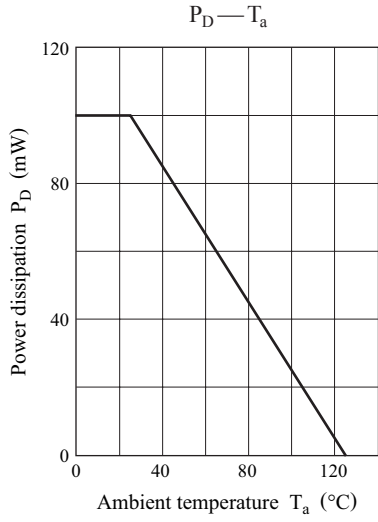
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	$V_{DSS}$	$I_D = -10 \mu\text{A}, V_{GS} = 0$	-30			V
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = -20 \text{V}, V_{GS} = 0$			-1.0	$\mu\text{A}$
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = \pm 10 \text{V}, V_{DS} = 0$			$\pm 10$	$\mu\text{A}$
Gate threshold voltage	$V_{TH}$	$I_D = -1.0 \mu\text{A}, V_{DS} = -3.0 \text{V}$	-0.5	-1.0	-1.5	V
Drain-source ON resistance	$R_{DS(on)}$	$I_D = -10 \text{mA}, V_{GS} = -2.5 \text{V}$		13	30	$\Omega$
		$I_D = -10 \text{mA}, V_{GS} = -4.0 \text{V}$		9	18	
Forward transfer admittance	$ Y_{fs} $	$I_D = -10 \text{mA}, V_{DS} = -3 \text{V}, f = 1 \text{kHz}$	20	40		mS
Short-circuit input capacitance (Common source)	$C_{iss}$	$V_{DS} = -3 \text{V}, V_{GS} = 0, f = 1 \text{MHz}$		12		pF
Short-circuit output capacitance (Common source)	$C_{oss}$				13	pF
Reverse transfer capacitance (Common source)	$C_{rss}$			7		pF
Turn-on time *	$t_{on}$	$V_{DD} = -3 \text{V}, V_{GS} = 0 \text{V to } -3 \text{V}, I_D = -10 \text{mA}$		300		ns
Turn-off time *	$t_{off}$	$V_{DD} = -3 \text{V}, V_{GS} = -3 \text{V to } 0 \text{V}, I_D = -10 \text{mA}$		400		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

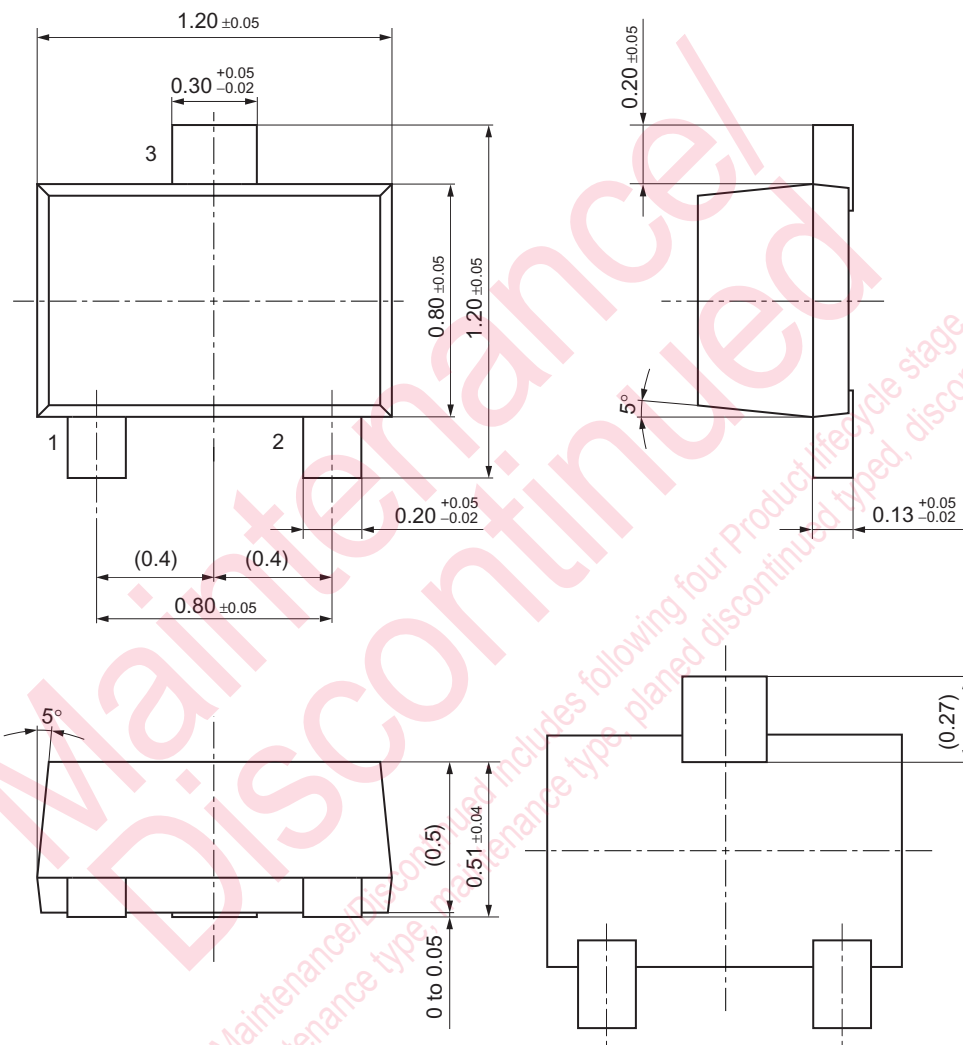
2. \*:  $t_{on}, t_{off}$  measurement circuit





SSSMini3-F2

Unit: mm



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